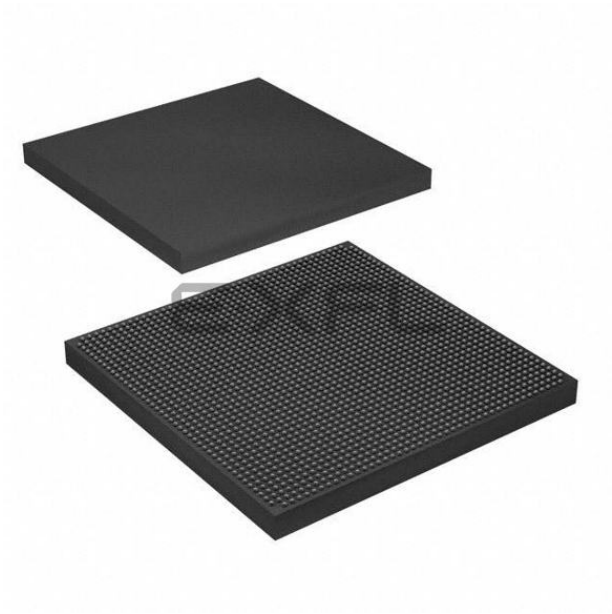
Intel - 5SGXEA5N1F45I2N Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	185000
Number of Logic Elements/Cells	490000
Total RAM Bits	46080000
Number of I/O	840
Number of Gates	-
Voltage - Supply	0.87V ~ 0.93V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1932-BBGA, FCBGA
Supplier Device Package	1932-FBGA, FC (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/intel/5sgxea5n1f45i2n

Table 1. Stratix V GX and GS Commercial and Industrial Speed Grade Offering (1), (2), (3) (Part 2 of 2)

Transceiver Speed Grade	Core Speed Grade							
	C1	C2, C2L	C3	C4	I2, I2L	I3, I3L	I3YY	I4
3 GX channel—8.5 Gbps	—	Yes	Yes	Yes	—	Yes	Yes (4)	Yes

Notes to Table 1:

(1) C = Commercial temperature grade; I = Industrial temperature grade.

(2) Lower number refers to faster speed grade.

(3) C2L, I2L, and I3L speed grades are for low-power devices.

(4) I3YY speed grades can achieve up to 10.3125 Gbps.

Table 2 li he ind rial and commercial peed grade for he S ra i V GT de ice .

Table 2. Stratix V GT Commercial and Industrial Speed Grade Offering (1), (2)

Transceiver Speed Grade	Core Speed Grade			
	C1	C2	I2	I3
2 GX channel—12.5 Gbps GT channel—28.05 Gbps	Yes	Yes	—	—
3 GX channel—12.5 Gbps GT channel—25.78 Gbps	Yes	Yes	Yes	Yes

Notes to Table 2:

(1) C = Commercial temperature grade; I = Industrial temperature grade.

(2) Lower number refers to faster speed grade.

Absolute Maximum Ratings

Ab ol e ma im m ra ing define he ma im m opera ing condi ion for S ra i V de ice . The al e are ba ed on e perimen cond c ed i h he de ice and heore ical modeling of breakdo n and damage mechani m . The f nc ional opera ion of he de ice i no implied for he e condi ion .

CAUTION

Condi ion o her han ho e li ed in Table 3 ma ca e permanen damage o he de ice. Addi ionall , de ice opera ion a he ab ol e ma im m ra ing for e ended period of ime ma ha e ad er e effec on he de ice.

Table 3. Absolute Maximum Ratings for Stratix V Devices (Part 1 of 2)

Symbol	Description	Minimum	Maximum	Unit
V_{CC}	Power supply for core voltage and periphery circuitry	–0.5	1.35	V
V_{CCPT}	Power supply for programmable power technology	–0.5	1.8	V
V_{CCPGM}	Power supply for configuration pins	–0.5	3.9	V
V_{CC_AUX}	Auxiliary supply for the programmable power technology	–0.5	3.4	V
V_{CCBAT}	Battery back-up power supply for design security volatile key register	–0.5	3.9	V
V_{CCPD}	I/O pre-driver power supply	–0.5	3.9	V
V_{CCIO}	I/O power supply	–0.5	3.9	V

I/O Pin Leakage Current

Table 9 li he S ra i V I/O pin leakage c rren pecifica ion .

Table 9. I/O Pin Leakage Current for Stratix V Devices (1)

Symbol	Description	Conditions	Min	Typ	Max	Unit
I_I	Input pin	V_I = 0 V to $V_{CCIOMAX}$	–30	—	30	µA
I_{OZ}	Tri-stated I/O pin	V_O = 0 V to $V_{CCIOMAX}$	–30	—	30	µA

Note to Table 9:

(1) If $V_O = V_{CCIO}$ to $V_{CCIOMax}$, 100 µA of leakage current per I/O is expected.

Bus Hold Specifications

Table 10 li he S ra i V de ice famil b hold pecifica ion .

Table 10. Bus Hold Parameters for Stratix V Devices

Parameter	Symbol	Conditions	V_{CCIO}										Unit
			1.2 V		1.5 V		1.8 V		2.5 V		3.0 V		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	I_{SUSL}	$V_{IN} > V_{IL}$ (maximum)	22.5	—	25.0	—	30.0	—	50.0	—	70.0	—	µA
High sustaining current	I_{SUSH}	$V_{IN} < V_{IH}$ (minimum)	–22.5	—	–25.0	—	–30.0	—	–50.0	—	–70.0	—	µA
Low overdrive current	I_{ODL}	$0V < V_{IN} < V_{CCIO}$	—	120	—	160	—	200	—	300	—	500	µA
High overdrive current	I_{ODH}	$0V < V_{IN} < V_{CCIO}$	—	–120	—	–160	—	–200	—	–300	—	–500	µA
Bus-hold trip point	V_{TRIP}	—	0.45	0.95	0.50	1.00	0.68	1.07	0.70	1.70	0.80	2.00	V

On-Chip Termination (OCT) Specifications

If o enable OCT calibra ion, calibra ion i a oma icall performed a po er- p for I/O connec ed o he calibra ion block. Table 11 li he S ra i V OCT ermina ion calibra ion acc rac pecifica ion .

Table 11. OCT Calibration Accuracy Specifications for Stratix V Devices (1) **(Part 1 of 2)**

Symbol	Description	Conditions	Calibration Accuracy				Unit
			C1	C2,I2	C3,I3, I3YY	C4,I4	
25- : R_S	Internal series termination with calibration (25- : setting)	V_{CCIO} = 3.0, 2.5, 1.8, 1.5, 1.2 V	±15	±15	±15	±15	%

Yo picall e he in erac i e E cel-ba ed Earl Po er E ima or before de igning he FPGA o ge a magni de e ima e of he de ice po er. The Q ar II Po erPla Po er Anal er pro ide be er q ali e ima e ba ed on he pecific of he de ign af er o comple e place-and-ro e. The Po erPla Po er Anal er can appl a combina ion of er-en ered, im la ion-deri ed, and e ima ed ignal ac i i ie ha , hen combined i h de ailed circ i model , ield er acc ra e po er e ima e .

For more informa ion abo po er e ima ion ool , refer o he *PowerPlay Early Power Estimator User Guide* and he *PowerPlay Power Analysis* chap er in he *Quartus II Handbook*.

Switching Characteristics

Thi ec ion pro ide performance charac eri ic of he S ra i V core and peripher block .

The e charac eri ic can be de igna ed a Preliminar or Final.

Preliminar charac eri ic are crea ed ing im la ion re l , proce da a, and o her kno n parame er . The i le of he e able ho he de igna ion a Preliminar .

Final n mber are ba ed on ac al ilicon charac eri a ion and e ing. The n mber reflec he ac al performance of he de ice nder or -ca e ilicon proce , ol age, and j nc ion empera re condi ion . There are no de igna ion on finali ed able .

Transceiver Performance Specifications

Thi ec ion de cribe ran cei er performance pecifica ion .

Table 23 li he S ra i V GX and GS ran cei er pecifica ion .

Table 23. Transceiver Specifications for Stratix V GX and GS Devices (1) (Part 1 of 7)

Symbol/ Description	Conditions	Transceiver Speed Grade 1			Transceiver Speed Grade 2			Transceiver Speed Grade 3			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Reference Clock											
Supported I/O Standards	Dedicated reference clock pin	1.2-V PCML, 1.4-V PCML, 1.5-V PCML, 2.5-V PCML, Differential LVPECL, LVDS, and HCSL									
	RX reference clock pin	1.4-V PCML, 1.5-V PCML, 2.5-V PCML, LVPECL, and LVDS									
Input Reference Clock Frequency (CMU PLL) (8)	—	40	—	710	40	—	710	40	—	710	MHz
Input Reference Clock Frequency (ATX PLL) (8)	—	100	—	710	100	—	710	100	—	710	MHz
Rise time	Measure at ±60 mV of differential signal (26)	—	—	400	—	—	400	—	—	400	ps
Fall time	Measure at ±60 mV of differential signal (26)	—	—	400	—	—	400	—	—	400	ps
Duty cycle	—	45	—	55	45	—	55	45	—	55	%
Spread-spectrum modulating clock frequency	PCI Express® (PCIe®)	30	—	33	30	—	33	30	—	33	kHz

Table 23. Transceiver Specifications for Stratix V GX and GS Devices (1) (Part 5 of 7)

Symbol/ Description	Conditions	Transceiver Speed Grade 1			Transceiver Speed Grade 2			Transceiver Speed Grade 3			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Programmable DC gain	DC Gain Setting = 0	—	0	—	—	0	—	—	0	—	dB
	DC Gain Setting = 1	—	2	—	—	2	—	—	2	—	dB
	DC Gain Setting = 2	—	4	—	—	4	—	—	4	—	dB
	DC Gain Setting = 3	—	6	—	—	6	—	—	6	—	dB
	DC Gain Setting = 4	—	8	—	—	8	—	—	8	—	dB
Transmitter											
Supported I/O Standards	—	1.4-V and 1.5-V PCML									
Data rate (Standard PCS)	—	600	—	12200	600	—	12200	600	—	8500/ 10312.5 (24)	Mbps
Data rate (10G PCS)	—	600	—	14100	600	—	12500	600	—	8500/ 10312.5 (24)	Mbps
Differential on-chip termination resistors	85- : setting	—	85 ± 20%	—	—	85 ± 20%	—	—	85 ± 20%	—	:
	100- : setting	—	100 ± 20%	—	—	100 ± 20%	—	—	100 ± 20%	—	:
	120- : setting	—	120 ± 20%	—	—	120 ± 20%	—	—	120 ± 20%	—	:
	150- : setting	—	150 ± 20%	—	—	150 ± 20%	—	—	150 ± 20%	—	:
V_{OCM} (AC coupled)	0.65-V setting	—	650	—	—	650	—	—	650	—	mV
V_{OCM} (DC coupled)	—	—	650	—	—	650	—	—	650	—	mV
Rise time (7)	20% to 80%	30	—	160	30	—	160	30	—	160	ps
Fall time (7)	80% to 20%	30	—	160	30	—	160	30	—	160	ps
Intra-differential pair skew	Tx V_{CM} = 0.5 V and slew rate of 15 ps	—	—	15	—	—	15	—	—	15	ps
Intra-transceiver block transmitter channel-to-channel skew	x6 PMA bonded mode	—	—	120	—	—	120	—	—	120	ps

Table 28. Transceiver Specifications for Stratix V GT Devices (Part 2 of 5) (1)

Symbol/ Description	Conditions	Transceiver Speed Grade 2			Transceiver Speed Grade 3			Unit
		Min	Typ	Max	Min	Typ	Max	
Transmitter REFCLK Phase Noise (622 MHz) (18)	100 Hz	—	—	-70	—	—	-70	dBc/Hz
	1 kHz	—	—	-90	—	—	-90	
	10 kHz	—	—	-100	—	—	-100	
	100 kHz	—	—	-110	—	—	-110	
	≥ 1 MHz	—	—	-120	—	—	-120	
Transmitter REFCLK Phase Jitter (100 MHz) (15)	10 kHz to 1.5 MHz (PCIe)	—	—	3	—	—	3	ps (rms)
RREF (17)	—	—	1800 ± 1%	—	—	1800 ± 1%	—	:
Transceiver Clocks								
fixedclk clock frequency	PCIe Receiver Detect	—	100 or 125	—	—	100 or 125	—	MHz
Reconfiguration clock (mgmt_clk_clk) frequency	—	100	—	125	100	—	125	MHz
Receiver								
Supported I/O Standards	—	1.4-V PCML, 1.5-V PCML, 2.5-V PCML, LVPECL, and LVDS						
Data rate (Standard PCS) (21)	GX channels	600	—	8500	600	—	8500	Mbps
Data rate (10G PCS) (21)	GX channels	600	—	12,500	600	—	12,500	Mbps
Data rate	GT channels	19,600	—	28,050	19,600	—	25,780	Mbps
Absolute V_{MAX} for a receiver pin (3)	GT channels	—	—	1.2	—	—	1.2	V
Absolute V_{MIN} for a receiver pin	GT channels	–0.4	—	—	–0.4	—	—	V
Maximum peak-to-peak differential input voltage V_{ID} (diff p-p) before device configuration (20)	GT channels	—	—	1.6	—	—	1.6	V
	GX channels	(8)						
Maximum peak-to-peak differential input voltage V_{ID} (diff p-p) after device configuration (16), (20)	GT channels V_{CCR_GTB} = 1.05 V (V_{ICM} = 0.65 V)	—	—	2.2	—	—	2.2	V
	GX channels	(8)						
Minimum differential eye opening at receiver serial input pins (4), (20)	GT channels	200	—	—	200	—	—	mV
	GX channels	(8)						

Table 31. PLL Specifications for Stratix V Devices (Part 3 of 3)

Symbol	Parameter	Min	Typ	Max	Unit
f_{RES}	Resolution of VCO frequency (f_{INPFD} = 100 MHz)	390625	5.96	0.023	Hz

Notes to Table 31:

(1) This specification is limited in the Quartus II software by the I/O maximum frequency. The maximum I/O frequency is different for each I/O standard.

(2) This specification is limited by the lower of the two: I/O f_{MAX} or f_{OUT} of the PLL.

(3) A high input jitter directly affects the PLL output jitter. To have low PLL output clock jitter, you must provide a clean clock source < 120 ps.

(4) f_{REF} is fIN/N when N = 1.

(5) Peak-to-peak jitter with a probability level of 10^{-12} (14 sigma, 99.99999999974404% confidence level). The output jitter specification applies to the intrinsic jitter of the PLL, when an input jitter of 30 ps is applied. The external memory interface clock output jitter specifications use a different measurement method and are available in Table 44 on page 52.

(6) The cascaded PLL specification is only applicable with the following condition:
a. Upstream PLL: 0.59Mhz dUpstream PLL BW < 1 MHz
b. Downstream PLL: Downstream PLL BW > 2 MHz

(7) High bandwidth PLL settings are not supported in external feedback mode.

(8) The external memory interface clock output jitter specifications use a different measurement method, which is available in Table 42 on page 50.

(9) The VCO frequency reported by the Quartus II software in the PLL Usage Summary section of the compilation report takes into consideration the VCO post-scale counter K value. Therefore, if the counter K has a value of 2, the frequency reported can be lower than the f_{VCO} specification.

(10) This specification only covers fractional PLL for low bandwidth. The f_{VCO} for fractional value range 0.05 - 0.95 must be t 1000 MHz, while f_{VCO} for fractional value range 0.20 - 0.80 must be t 1200 MHz.

(11) This specification only covered fractional PLL for low bandwidth. The f_{VCO} for fractional value range 0.05-0.95 must be t 1000 MHz.

(12) This specification only covered fractional PLL for low bandwidth. The f_{VCO} for fractional value range 0.20-0.80 must be t 1200 MHz.

DSP Block Specifications

Table 32 li he S ra i V DSP block performance pecifica ion .

Table 32. Block Performance Specifications for Stratix V DSP Devices (Part 1 of 2)

Mode	Peformance							Unit
	C1	C2, C2L	I2, I2L	C3	I3, I3L, I3YY	C4	I4	
Modes using one DSP								
Three 9 x 9	600	600	600	480	480	420	420	MHz
One 18 x 18	600	600	600	480	480	420	400	MHz
Two partial 18 x 18 (or 16 x 16)	600	600	600	480	480	420	400	MHz
One 27 x 27	500	500	500	400	400	350	350	MHz
One 36 x 18	500	500	500	400	400	350	350	MHz
One sum of two 18 x 18(One sum of 2 16 x 16)	500	500	500	400	400	350	350	MHz
One sum of square	500	500	500	400	400	350	350	MHz
One 18 x 18 plus 36 (a x b) + c	500	500	500	400	400	350	350	MHz
Modes using two DSPs								
Three 18 x 18	500	500	500	400	400	350	350	MHz
One sum of four 18 x 18	475	475	475	380	380	300	300	MHz
One sum of two 27 x 27	465	465	450	380	380	300	290	MHz
One sum of two 36 x 18	475	475	475	380	380	300	300	MHz
One complex 18 x 18	500	500	500	400	400	350	350	MHz
One 36 x 36	475	475	475	380	380	300	300	MHz

Periphery Performance

Thi ec ion de cribe peripher performance, incl ding high- peed I/O and e ernal memor in erface.

I/O performance ppor e eral em in erface , ch a he LVDS high- peed I/O in erface, e ernal memor in erface, and he PCI/PCI-X b in erface. General-p rpo e I/O andard ch a 3.3-, 2.5-, 1.8-, and 1.5-LVTTL/LVCMOS are capable of a pical 167 MH and 1.2-LVCMOS a 100 MH in erfacing freq enc i h a 10 pF load.

☞ The ac al achie able freq enc depend on de ign- and em- pecific fac or . En re proper iming clo re in o r de ign and perform HSPICE/IBIS im la ion ba ed on o r pecific de ign and em e p o de ermine he ma im m achie able freq enc in o r em.

High-Speed I/O Specification

Table 36 li high- peed I/O iming for S ra i V de ice .

Table 36. High-Speed I/O Specifications for Stratix V Devices (1), (2) (Part 1 of 4)

Symbol	Conditions	C1			C2, C2L, I2, I2L			C3, I3, I3L, I3YY			C4,I4			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK_in} (input clock frequency) True Differential I/O Standards	Clock boost factor W = 1 to 40 (4)	5	—	800	5	—	800	5	—	625	5	—	525	MHz
f_{HSCLK_in} (input clock frequency) Single Ended I/O Standards (3)	Clock boost factor W = 1 to 40 (4)	5	—	800	5	—	800	5	—	625	5	—	525	MHz
f_{HSCLK_in} (input clock frequency) Single Ended I/O Standards	Clock boost factor W = 1 to 40 (4)	5	—	520	5	—	520	5	—	420	5	—	420	MHz
f_{HSCLK_OUT} (output clock frequency)	—	5	—	800	5	—	800	5	—	625 (5)	5	—	525 (5)	MHz

Table 36. High-Speed I/O Specifications for Stratix V Devices (1), (2) (Part 2 of 4)

Symbol	Conditions	C1			C2, C2L, I2, I2L			C3, I3, I3L, I3YY			C4,I4			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Transmitter														
True Differential I/O Standards - f_{HSDR} (data rate)	SERDES factor J = 3 to 10 (9), (11), (12), (13), (14), (15), (16)	(6)	—	1600	(6)	—	1434	(6)	—	1250	(6)	—	1050	Mbps
	SERDES factor J t 4 LVDS TX with DPA (12), (14), (15), (16)	(6)	—	1600	(6)	—	1600	(6)	—	1600	(6)	—	1250	Mbps
	SERDES factor J = 2, uses DDR Registers	(6)	—	(7)	(6)	—	(7)	(6)	—	(7)	(6)	—	(7)	Mbps
	SERDES factor J = 1, uses SDR Register	(6)	—	(7)	(6)	—	(7)	(6)	—	(7)	(6)	—	(7)	Mbps
Emulated Differential I/O Standards with Three External Output Resistor Networks - f_{HSDR} (data rate) (10)	SERDES factor J = 4 to 10 (17)	(6)	—	1100	(6)	—	1100	(6)	—	840	(6)	—	840	Mbps
x Jitter - True Differential I/O Standards	Total Jitter for Data Rate 600 Mbps - 1.25 Gbps	—	—	160	—	—	160	—	—	160	—	—	160	ps
	Total Jitter for Data Rate < 600 Mbps	—	—	0.1	—	—	0.1	—	—	0.1	—	—	0.1	UI
x Jitter - Emulated Differential I/O Standards with Three External Output Resistor Network	Total Jitter for Data Rate 600 Mbps - 1.25 Gbps	—	—	300	—	—	300	—	—	300	—	—	325	ps
	Total Jitter for Data Rate < 600 Mbps	—	—	0.2	—	—	0.2	—	—	0.2	—	—	0.25	UI

Table 42. Memory Output Clock Jitter Specification for Stratix V Devices (1), (Part 2 of 2) (2), (3)

Clock Network	Parameter	Symbol	C1		C2, C2L, I2, I2L		C3, I3, I3L, I3YY		C4,I4		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
PHY Clock	Clock period jitter	$t_{JIT(per)}$	–25	25	–25	25	–30	30	–35	35	ps
	Cycle-to-cycle period jitter	$t_{JIT(cc)}$	–50	50	–50	50	–60	60	–70	70	ps
	Duty cycle jitter	$t_{JIT(duty)}$	–37.5	37.5	–37.5	37.5	–45	45	–56	56	ps

Notes to Table 42:

(1) The clock jitter specification applies to the memory output clock pins generated using differential signal-splitter and DDIO circuits clocked by a PLL output routed on a PHY, regional, or global clock network as specified. Altera recommends using PHY clock networks whenever possible.

(2) The clock jitter specification applies to the memory output clock pins clocked by an integer PLL.

(3) The memory output clock jitter is applicable when an input jitter of 30 ps peak-to-peak is applied with bit error rate (BER) -12, equivalent to 14 sigma.

OCT Calibration Block Specifications

Table 43 li he OCT calibra ion block pecifica ion for S ra i V de ice .

Table 43. OCT Calibration Block Specifications for Stratix V Devices

Symbol	Description	Min	Typ	Max	Unit
OCTUSRCLK	Clock required by the OCT calibration blocks	—	—	20	MHz
T_{OCTCAL}	Number of OCTUSRCLK clock cycles required for OCT R_S/R_T calibration	—	1000	—	Cycles
$T_{OCTSHIFT}$	Number of OCTUSRCLK clock cycles required for the OCT code to shift out	—	32	—	Cycles
T_{RS_RT}	Time required between the dyn_term_ctrl and oe signal transitions in a bidirectional I/O buffer to dynamically switch between OCT R_S and R_T (Figure 10)	—	2.5	—	ns

Fig re 10 ho he iming diagram for he oe and dyn_term_ctrl ignal .
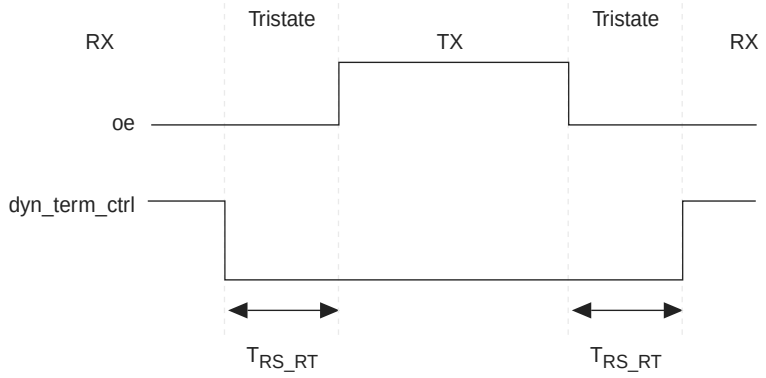
Figure 10. Timing Diagram for oe and dyn_term_ctrl Signals